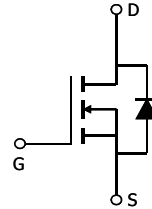


General Description

The AO4476A combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is suitable for use as a high side switch in SMPS and general purpose applications.

Features

| | |
|------------------------------------|------------------|
| V_{DS} | 30V |
| I_D (at $V_{GS}=10V$) | 15A |
| $R_{DS(ON)}$ (at $V_{GS}=10V$) | < 7.7m Ω |
| $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) | < 10.8m Ω |



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|--|------------------|------------------------|------------------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | I_D | $T_A=25^\circ\text{C}$ | 15 |
| | | $T_A=70^\circ\text{C}$ | 12 |
| Pulsed Drain Current ^C | I_{DM} | 110 | A |
| Avalanche Current ^C | I_{AS}, I_{AR} | 27 | A |
| Avalanche energy $L=0.1\text{mH}$ ^C | E_{AS}, E_{AR} | 36 | mJ |
| Power Dissipation ^B | P_D | $T_A=25^\circ\text{C}$ | 3.1 |
| | | $T_A=70^\circ\text{C}$ | 2 |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|---|-----------------|--------------|-----|---------------------------|
| Maximum Junction-to-Ambient ^A | $R_{\theta JA}$ | 31 | 40 | $^\circ\text{C}/\text{W}$ |
| Maximum Junction-to-Ambient ^{A, D} | | Steady-State | 59 | 75 |
| Maximum Junction-to-Lead | $R_{\theta JL}$ | 16 | 24 | $^\circ\text{C}/\text{W}$ |

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|---------------------------------------|---|------|------|--------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =250μA, V _{GS} =0V | 30 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =30V, V _{GS} =0V T _J =55°C | | | 1 5 | μA |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} = ±20V | | | 100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 1.5 | 1.98 | 2.5 | V |
| I _{D(ON)} | On state drain current | V _{GS} =10V, V _{DS} =5V | 110 | | | A |
| R _{DS(ON)} | Static Drain-Source On-Resistance | V _{GS} =10V, I _D =15A T _J =125°C | | 6.4 | 7.7 | mΩ |
| | | V _{GS} =4.5V, I _D =12A | | 8.6 | 10.8 | |
| g _{FS} | Forward Transconductance | V _{DS} =5V, I _D =15A | | 45 | | S |
| V _{SD} | Diode Forward Voltage | I _S =1A, V _{GS} =0V | | 0.74 | 1 | V |
| I _S | Maximum Body-Diode Continuous Current | | | | 4 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =15V, f=1MHz | 920 | 1150 | 1380 | pF |
| C _{oss} | Output Capacitance | | 125 | 180 | 235 | pF |
| C _{riss} | Reverse Transfer Capacitance | | 60 | 105 | 150 | pF |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, f=1MHz | 0.55 | 1.1 | 1.65 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| Q _{g(10V)} | Total Gate Charge | V _{GS} =10V, V _{DS} =15V, I _D =15A | 16 | 20 | 24 | nC |
| Q _{g(4.5V)} | Total Gate Charge | | 7.6 | 9.5 | 11.4 | nC |
| Q _{gs} | Gate Source Charge | | 2 | 2.7 | 3.2 | nC |
| Q _{gd} | Gate Drain Charge | | 3 | 5 | 7 | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =10V, V _{DS} =15V, R _L =1Ω, R _{GEN} =3Ω | | 6.5 | | ns |
| t _r | Turn-On Rise Time | | | 2 | | ns |
| t _{D(off)} | Turn-Off DelayTime | | | 17 | | ns |
| t _f | Turn-Off Fall Time | | | 3.5 | | ns |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =15A, dI/dt=500A/μs | 7 | 8.7 | 10.5 | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =15A, dI/dt=500A/μs | 11 | 13.5 | 16 | nC |

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

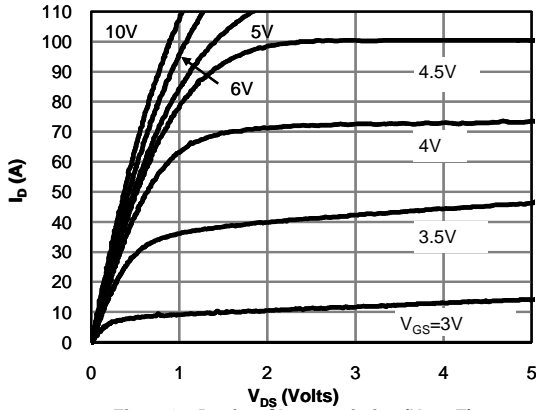


Figure 1: On-Region Characteristics (Note E)

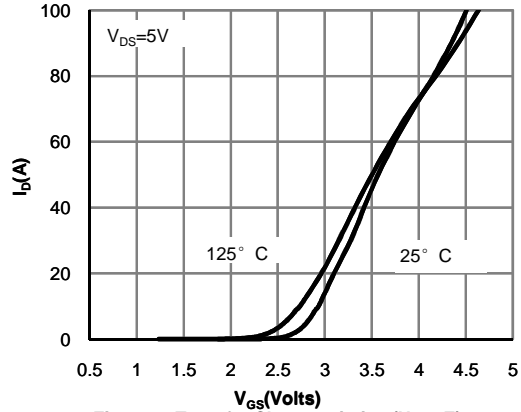


Figure 2: Transfer Characteristics (Note E)

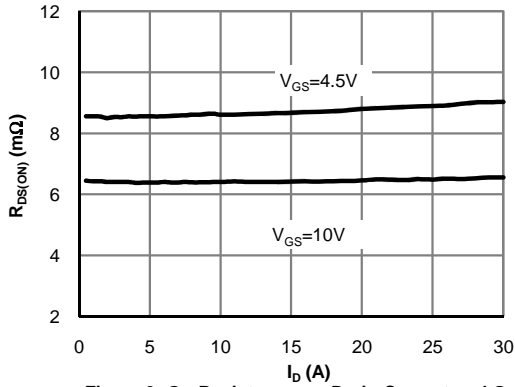


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

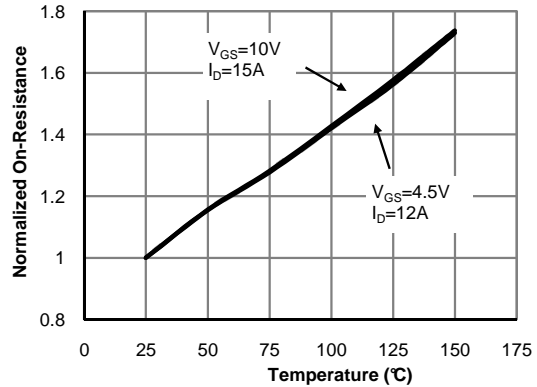


Figure 4: On-Resistance vs. Junction Temperature (Note E)

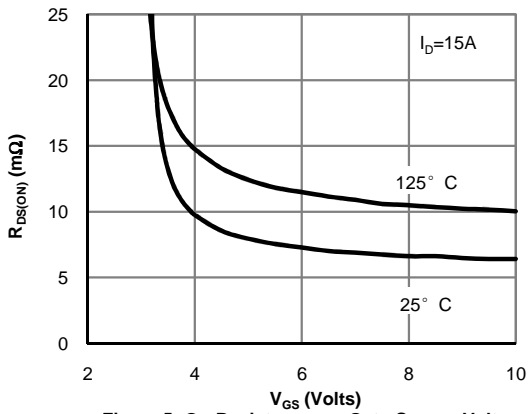


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

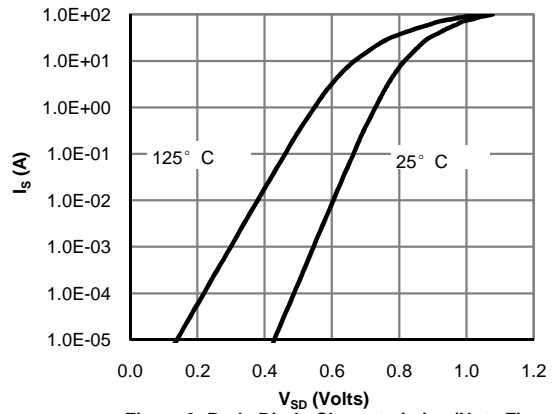
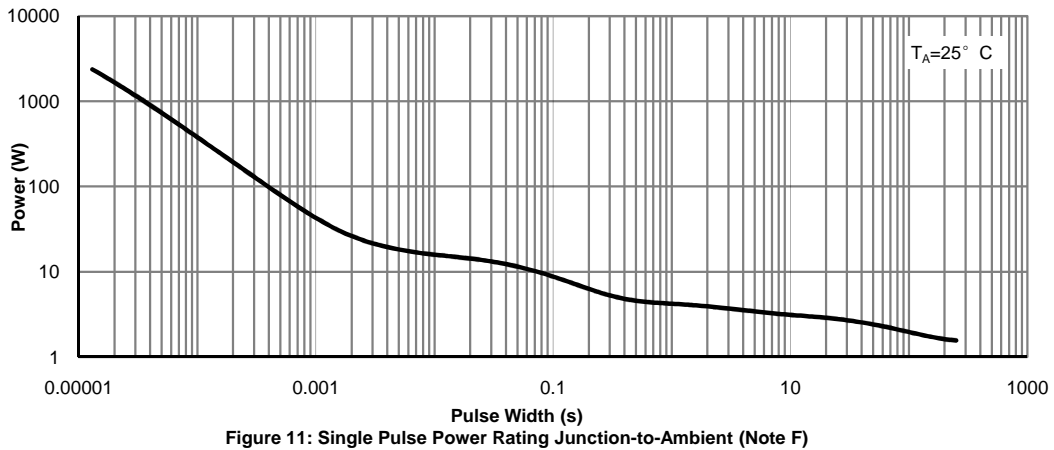
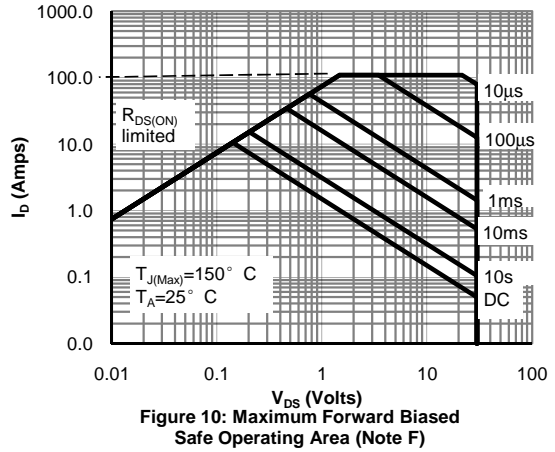
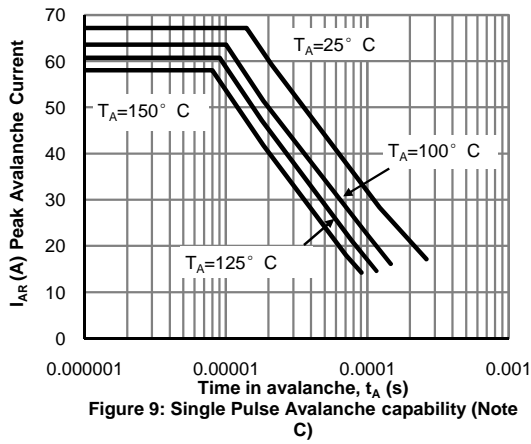
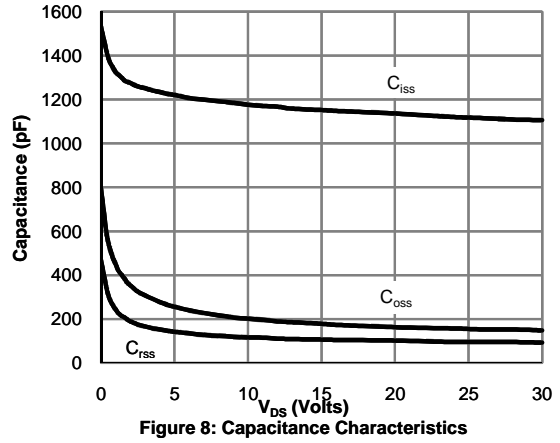
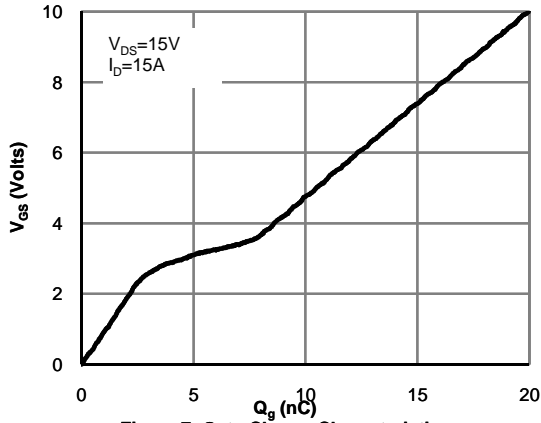


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

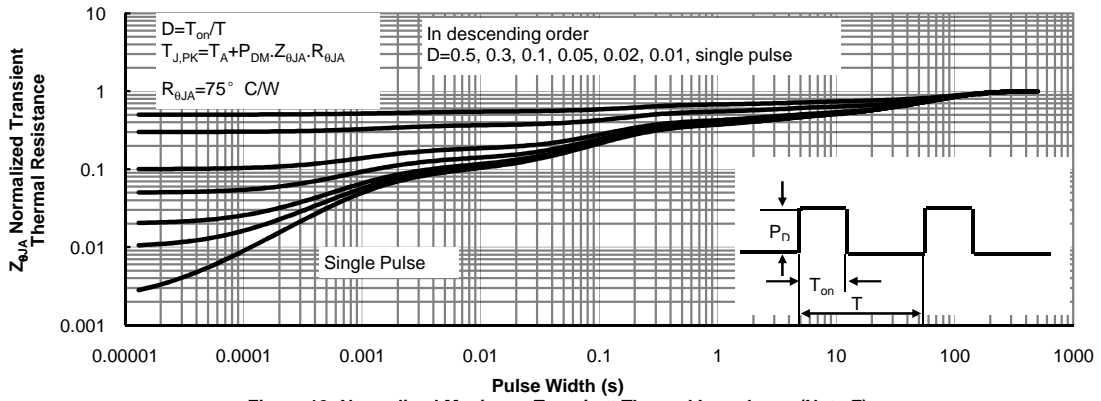
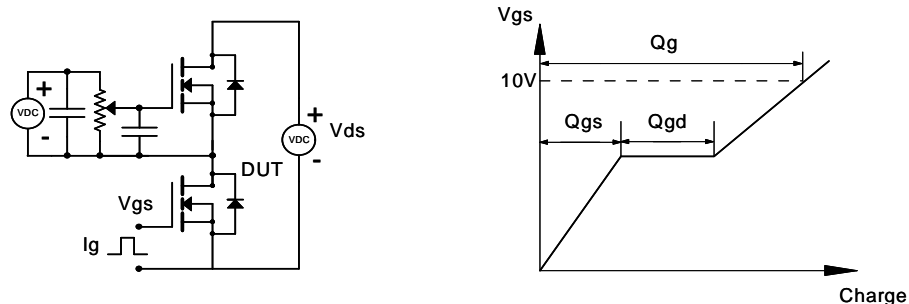
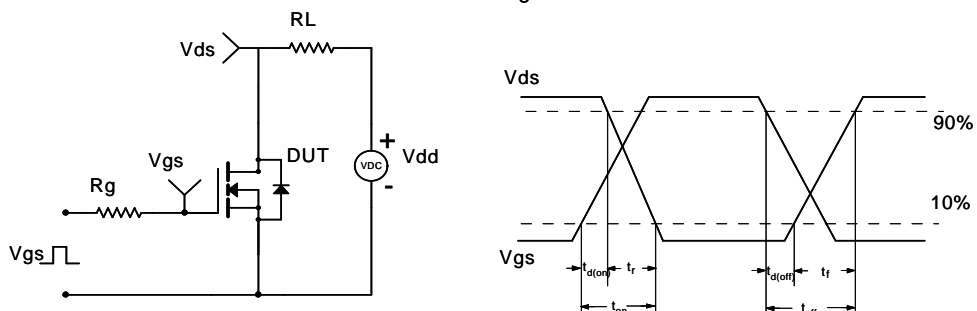


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

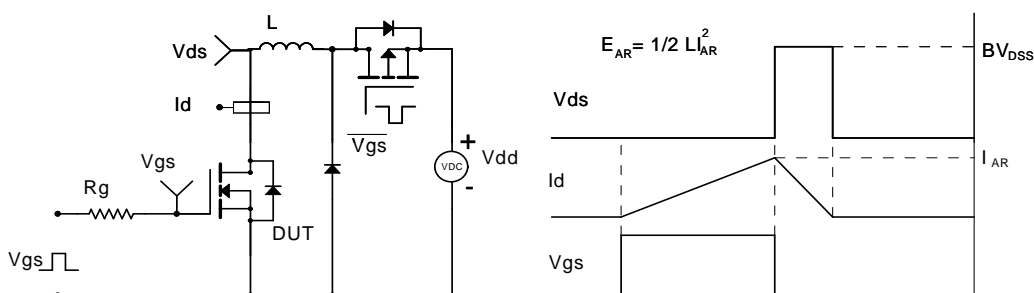
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

